

N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
150	0.052 at V _{GS} = 10 V	25		
	0.060 at V _{GS} = 6 V	23		

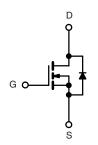
FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 % R_g Tested



APPLICATIONS

Primary Side Switch



N-Channel MOSFET

TO-252	
<u> </u>	
G D S	Drain Connected to Tab
Top View	

Ordering Information:

SUD25N15-52-E3 (Lead (Pb)- free)

ABSOLUTE MAXIMUM RATINGS $T_A =$	25 °C, unless other	wise noted		
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	150	V
Gate-Source Voltage		V _{GS}	± 20	v
Ocation and Durin Comment (T., 175 (O))	T _C = 25 °C	1	25	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	l _D	14.5	
Pulsed Drain Current		I _{DM}	50	А
Continuous Source Current (Diode Conduction)	I _S	25		
Avalanche Current	I _{AR}	25		
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	31	mJ
M : D D: : ::	T _C = 25 °C	P _D	136 ^b	14/
Maximum Power Dissipation	T _A = 25 °C		3 ^a	W
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	15	18	°C/W	
Junction-to-Ambient*	Steady State		40	50		
Junction-to-Case (Drain)		R _{thJC}	0.85	1.1		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	e Breakdown Voltage V_{DS} $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		150			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2		4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 150 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		V _{DS} = 150 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			Α	
		V _{GS} = 10 V, I _D = 5 A		0.042	0.052		
5	В	V _{GS} = 10 V, I _D = 5 A, T _J = 125 °C			0.109		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 5 A, T _J = 175 °C			0.145	Ω	
		V _{GS} = 6 V, I _D = 5 A		0.047	0.060		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 25 A		40		S	
Dynamic ^a							
Input Capacitance	C _{iss}			1725			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		216		pF	
Reverse Transfer Capacitance	C _{rss}			100			
Total Gate Charge ^c	Qg			33	40		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 25 \text{ A}$		9		nC	
Gate-Drain Charge ^c	Q _{gd}			12			
Gate Resistance	R _g		1		3	Ω	
Turn-On Delay Time ^c	t _{d(on)}			15	25		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_L = 3 \Omega$		70	100		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 25 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		25	40	ns	
Fall Time ^c	t _f			60	90	ı	
Source-Drain Diode Ratings and Cha	racteristics ⁻	Г _С = 25 °С					
Pulsed Current	I _{SM}				50	Α	
Diode Forward Voltage ^b	V_{SD}	I _F = 25 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 25 A, dl/dt = 100 A/μs		95	140	ns	

Notes:

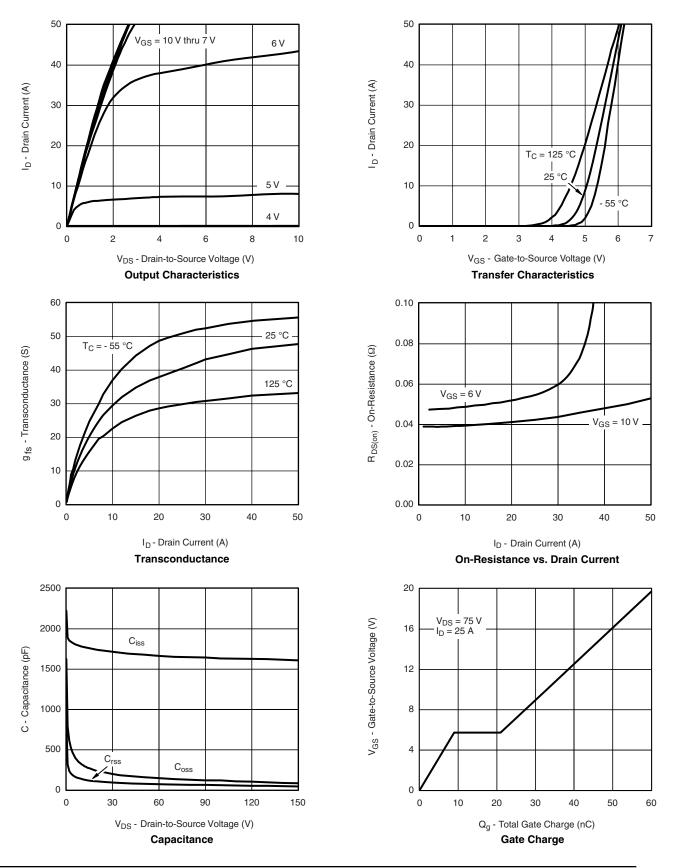
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μs , duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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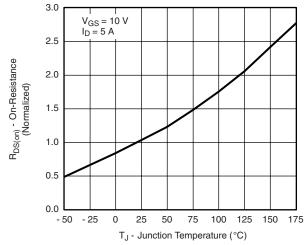
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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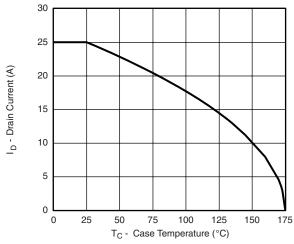


On-Resistance vs. Junction Temperature

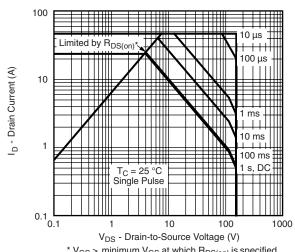
T_J = 150 °C T_J = 150 °C T_J = 25 °C T_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

THERMAL RATINGS

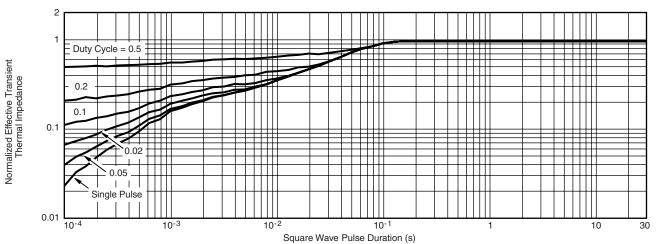


Maximum Avalanche Drain Current vs. Case Temperature



* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

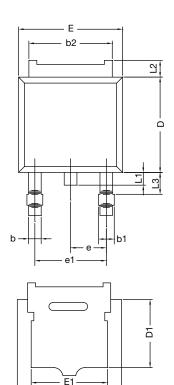
Safe Operating Area

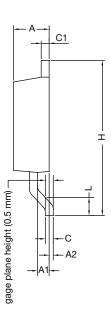


Normalized Thermal Transient Impedance, Junction-to-Case

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TO-252AA CASE OUTLINE





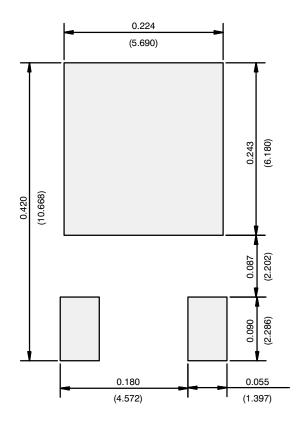
	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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